

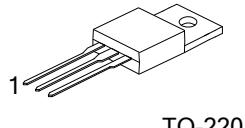
UF1010A

Power MOSFET

N-CHANNEL POWER MOSFET

■ DESCRIPTION

By using high technology, UTC **UF1010A** has the features, such as low $R_{DS(ON)}$, fast switching and low gate charge. Like features of all power MOSFET devices, UTC **UF1010A** can satisfy almost all the requirements of high efficient devices from customers.

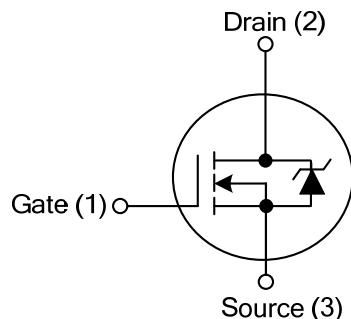


TO-220

■ FEATURES

- * $R_{DS(ON)} < 12 \text{ m}\Omega @ V_{GS} = 10V$
- * Ultra low gate charge : 130 nC
- * Low $C_{RSS} = 140 \text{ pF}(\text{typ.})$
- * Fast switching capability
- * Avalanche energy specified
- * Improved dv/dt capability
- * High ruggedness

■ SYMBOL



■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
UF1010AL-TA3-T	UF1010AG-TA3-T	TO-220	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

UF1010AL-TA3-T (1)Packing Type (2)Package Type (3)Lead Free	(1) T: Tube (2) TA3: TO-220 (3) G: Halogen Free, L: Lead Free
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■ ABSOLUTE MAXIMUM RATINGS ($T_J=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Gate to Source Voltage		V_{GSS}	± 20	V
Drain Current	Continuous ($V_{GS}=10\text{V}$)	I_D	84	A
	Pulsed (Note 2)	I_{DM}	330	
Avalanche Current (Note 2)		I_{AR}	50	A
Avalanche Energy	Repetitive (Note 2)	E_{AR}	17	mJ
	Single Pulsed (Note 3)	E_{AS}	1180	mJ
Power Dissipation ($T_c=25^\circ\text{C}$)		P_D	200	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Pulse width limited by $T_{J(\text{MAX})}$

3. $T_J=25^\circ\text{C}$, $L=260\mu\text{H}$, $R_G=25\Omega$, $I_{AS}=50\text{A}$

■ THERMAL DATA

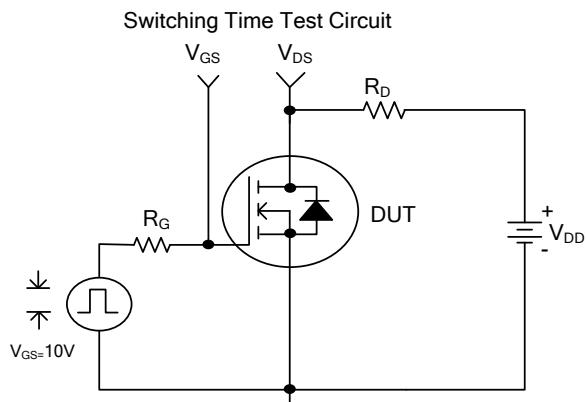
PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	62	$^\circ\text{C}/\text{W}$
Junction to Case	θ_{JC}	0.75	$^\circ\text{C}/\text{W}$

■ ELECTRICAL CHARACTERISTICS ($T_J=25^\circ\text{C}$, unless otherwise specified)

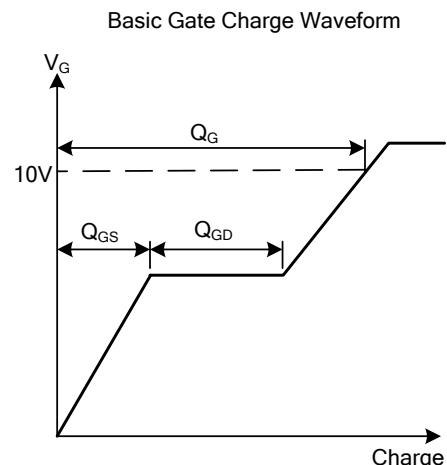
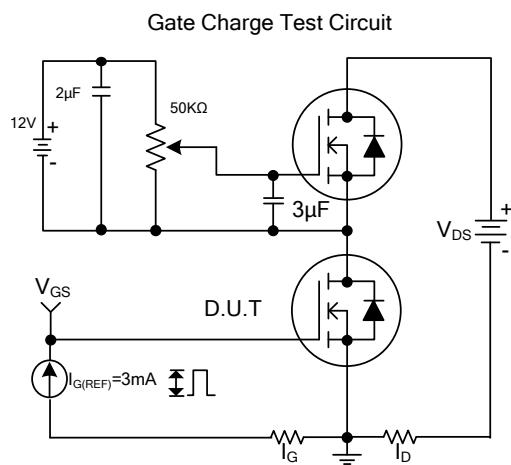
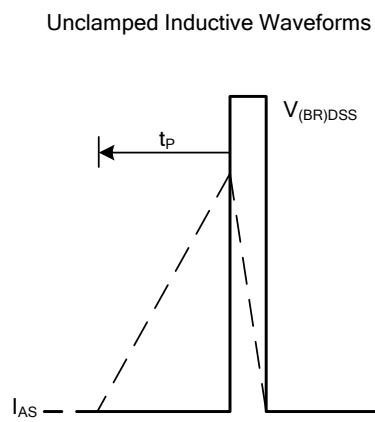
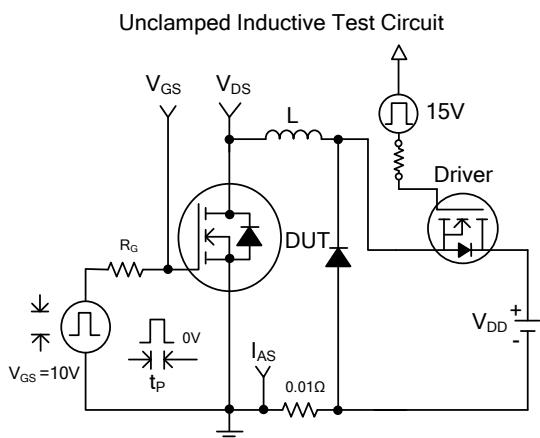
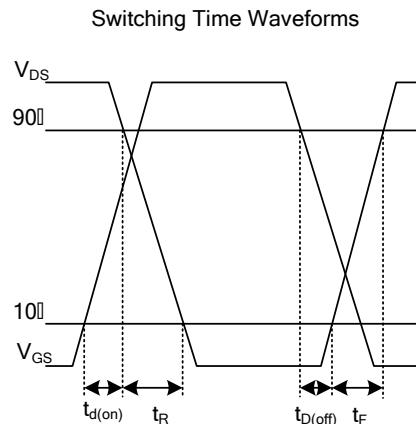
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0\text{ V}$, $I_D=250\mu\text{A}$	60			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=60\text{ V}$, $V_{GS}=0\text{ V}$		25		μA
		$V_{DS}=48\text{ V}$, $V_{GS}=0\text{ V}$, $T_J=150^\circ\text{C}$		250		μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20\text{ V}$, $V_{DS}=0\text{ V}$			± 100	nA
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	Reference to 25°C , $I_D=1\text{mA}$		0.064		$\text{V}/^\circ\text{C}$
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(\text{TH})}$	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	2.0		4.0	V
Static Drain-Source On Resistance (Note)	$R_{DS(\text{ON})}$	$V_{GS}=10\text{ V}$, $I_D=50\text{A}$			12	$\text{m}\Omega$
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	$V_{DS}=25\text{V}$, $V_{GS}=0\text{ V}$, $f=1\text{MHz}$		3210		pF
Output Capacitance	C_{OSS}			690		pF
Reverse Transfer Capacitance	C_{RSS}			140		pF
SWITCHING PARAMETERS						
Total Gate Charge	Q_G	$I_D=50\text{A}$, $V_{DS}=48\text{V}$, $V_{GS}=10\text{V}$			130	nC
Gate-to-Source Charge	Q_{GS}				28	nC
Gate-to-Drain ("Miller") Charge	Q_{GD}				44	nC
Turn ON Delay Time	$t_{D(\text{ON})}$	$V_{DD}=30\text{V}$, $I_D=50\text{A}$, $R_G=3.6\Omega$		12		ns
Turn ON Rise Time	t_R			78		ns
Turn OFF Delay Time	$t_{D(\text{OFF})}$			48		ns
Turn OFF Fall Time	t_F			53		ns
Internal Drain Inductance	L_D			4.5		nH
Internal Source Inductance	L_S			7.5		nH
Diode Forward Voltage	V_{SD}	$T_J=25^\circ\text{C}$, $I_S=50\text{A}$, $V_{GS}=0\text{V}$			1.3	V
Maximum Continuous Drain-Source Diode Forward Current	I_S				84	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				330	A
Reverse Recovery Time	t_{RR}	$T_J=25^\circ\text{C}$, $I_F=50\text{A}$, $di/dt=100\text{A}/\mu\text{s}$		73	110	ns
Reverse Recovery Charge	Q_{RR}			220	330	nC

Note: Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.

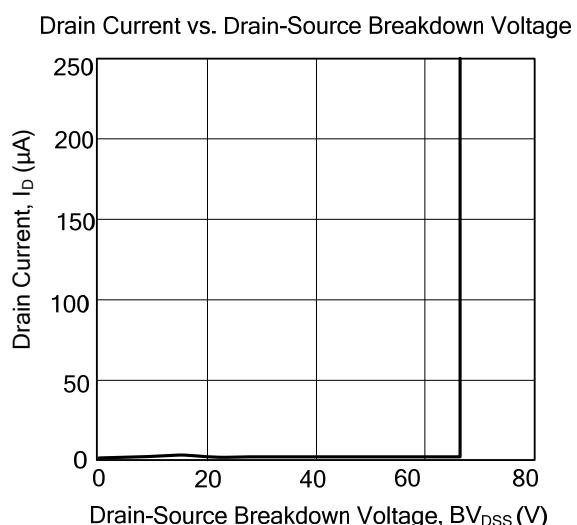
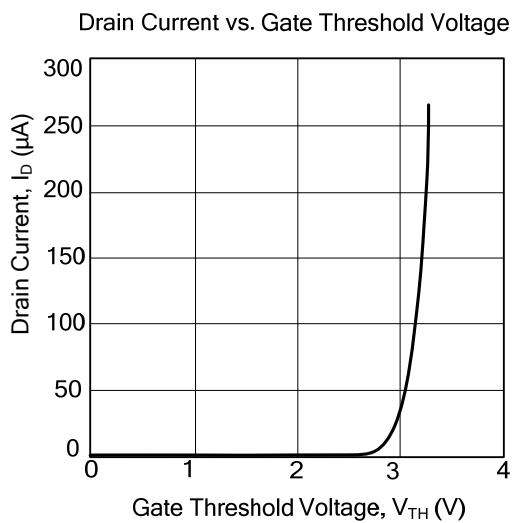
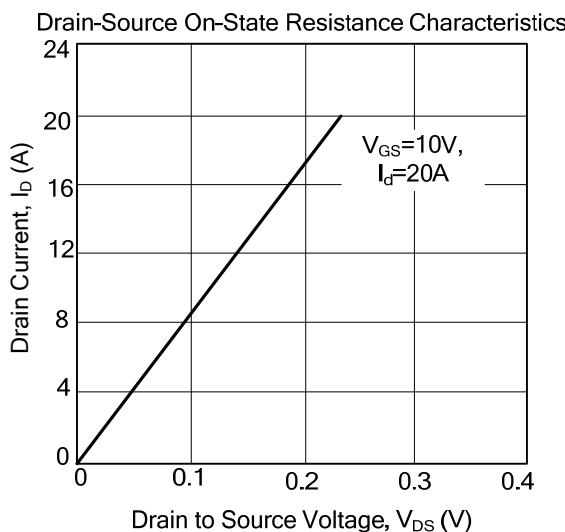
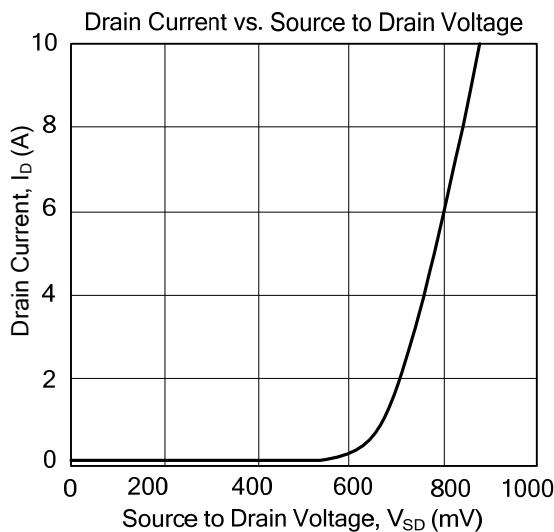
■ TEST CIRCUITS AND WAVEFORMS



Pulse Width≤1μs Duty Cycle≤0.1%



■ TYPICAL CHARACTERISTICS



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